

INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)		ATTY. DOCKET NO. <b>43889-951</b>	SERIAL NO. <b>(Divisional of Serial No. 08/965,892) 09/610,640</b>
		APPLICANT <b>Koji ERIGUCHI, et al.</b>	
		FILING DATE <b>July 05, 2000</b>	GROUP <b>2825</b>

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## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
CME	4,652,757	3/87	Carver	—	—	—
CME	4,750,822	6/88	Rosencwaig et al.	—	—	—
CME	5,260,772	11/93	Pollak et al.	—	—	—
CME	5,536,936	7/96	Drevillon et al.	—	—	—
CME	4,211,488	7/80	Kleinknecht	—	—	—
CME	5,365,334	11/15/94	Bottka	—	—	—
CME	5,379,109	1/3/95	Gaskill et al.	—	—	—
CME	5,313,044	5/17/94	Massoud et al.	—	—	—
CME	5,314,831	5/24/94	Hirae et al.	—	—	—
CME	5,663,657	9/2/97	Lagowski et al.	—	—	—

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
CME	0655620	11/29/94	Europe	—	—		

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

CME	"Supervisory Run-To-Run Control of Polysilicon Gate Etch Using In Situ Ellipsometry", by Butlers et al., IEEE Transaction on Semiconductor Manufacturing, Vol. 7, No. 2, May 1, 1995, pp. 193-201.
CME	"Measurement of Damage Profile in Semiconductors: A Sensitive Optical Technique", by Shwe et al., Applied Physics Letters, Vol. 62, No. 5, February 1, 1993, pp. 516-518.

EXAMINER <i>C. Kuehast</i>	DATE CONSIDERED <i>7-31-02</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.